

5.5: A 3.2 to 4GHz, 0.25μm CMOS Frequency Synthesizer for IEEE 802.11a/b/g WLAN

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Outline

■ System Requirements

**■ Architecture and Circuit
Description**

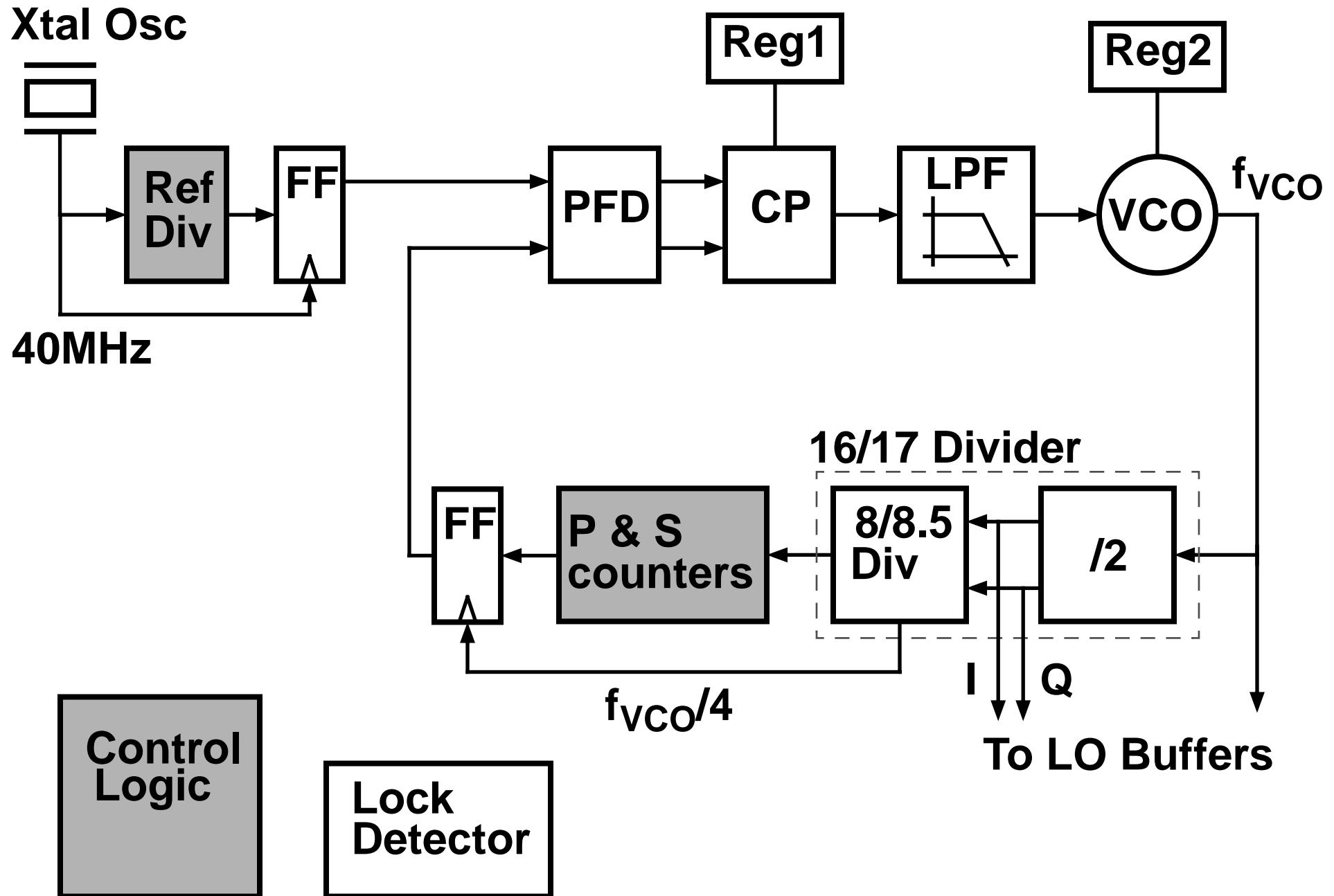
■ Measurements

■ Conclusions

Design Goals

- Tuning Range 3.2 - 4.0 GHz
- Reference Frequencies:
13.33M, 6.66M, 3.33M, 10M
- Drive LO Buffers at f_{VCO} and
I,Q LO Buffers at $f_{VCO}/2$
- Low Phase Noise
- Low Spurs

Synthesizer Block Diagram



Design Choices

■ Low VCO gain

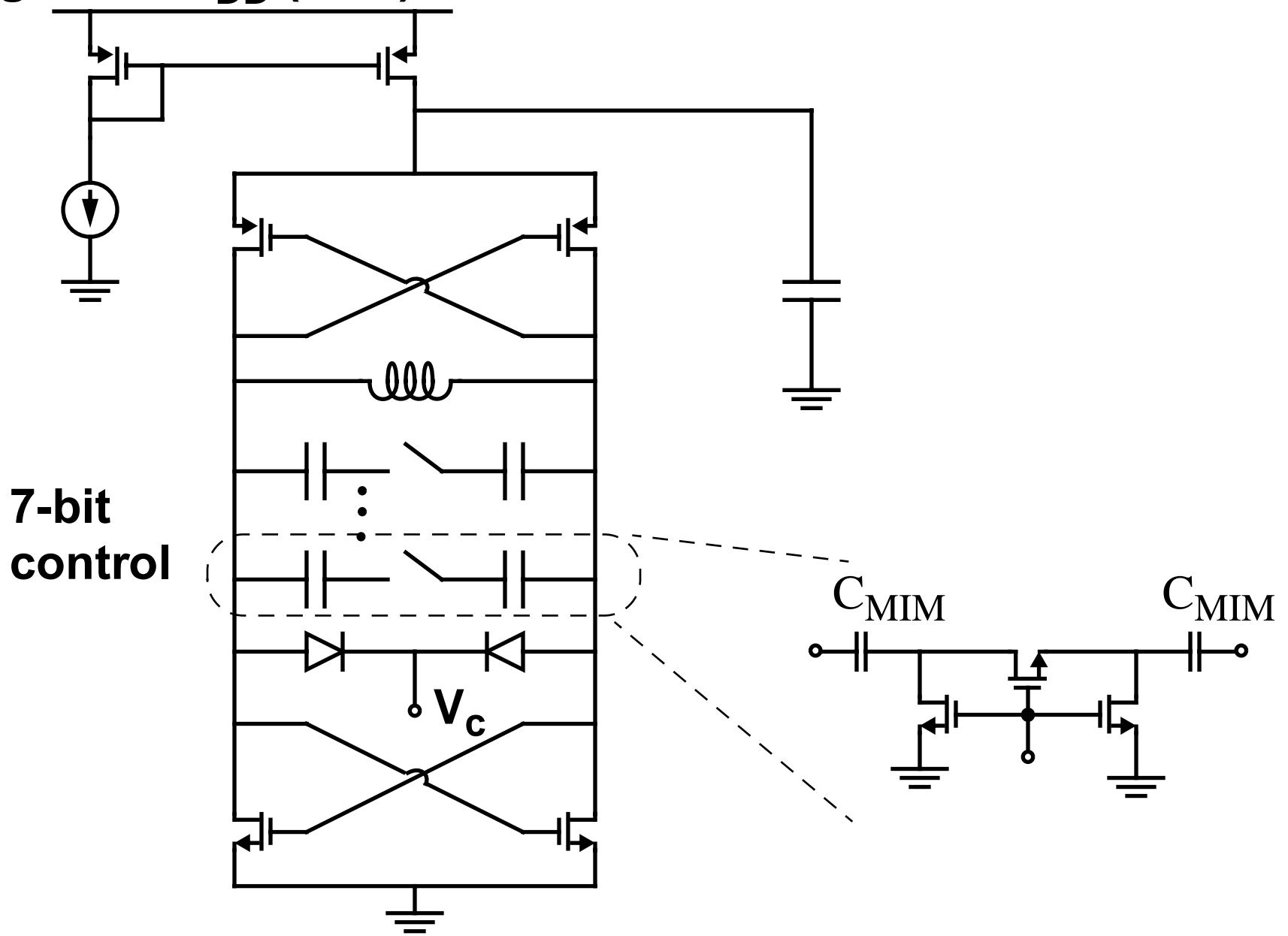
- Good VCO phase noise
- Low LPF resistor noise contribution

■ High charge pump current

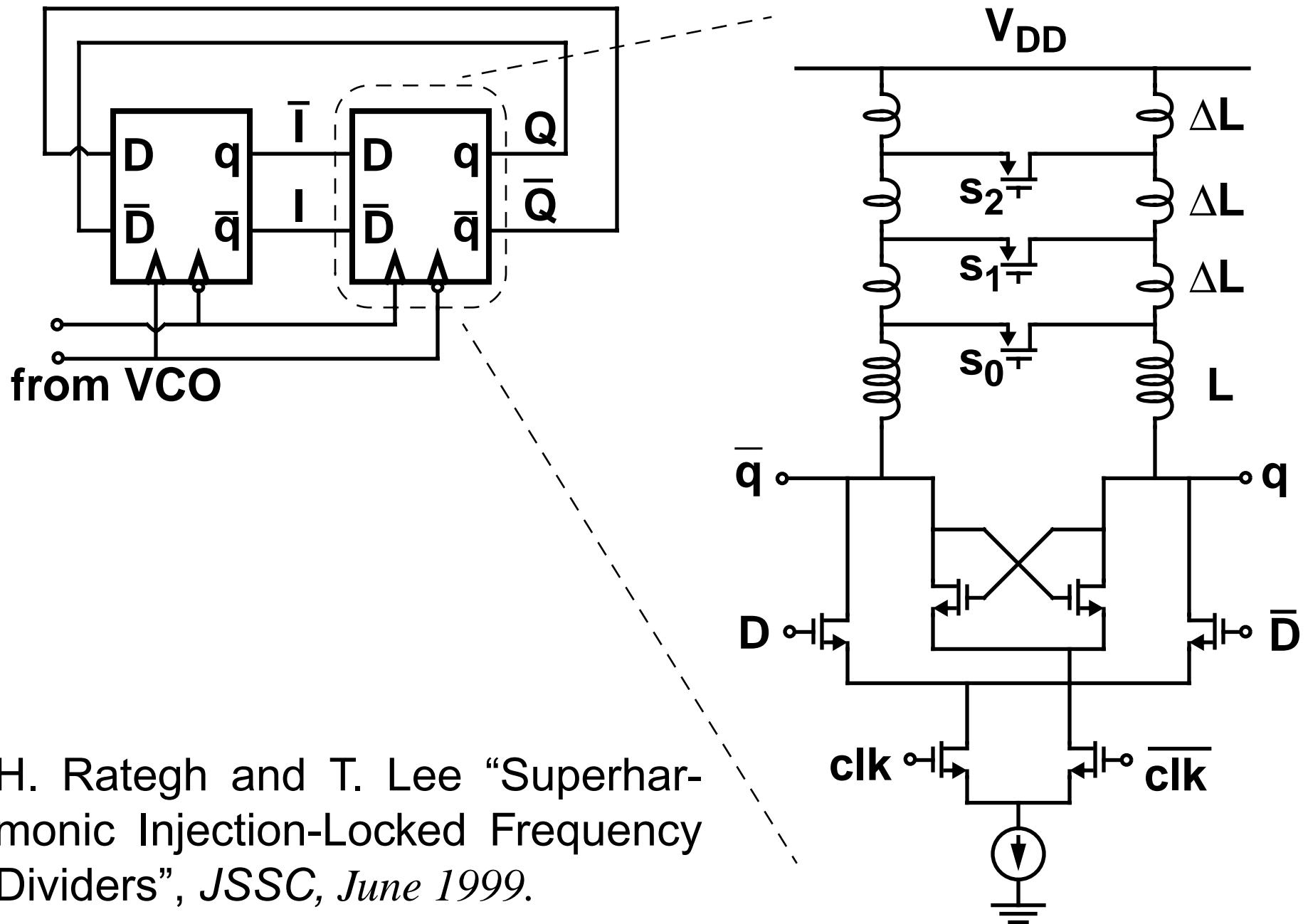
- Low LPF resistor noise contribution
- Low charge pump noise

Voltage Controlled Oscillator (VCO)

Regulated V_{DD} (2.5V)

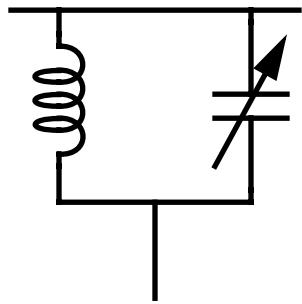


High-Frequency Divide-by-2



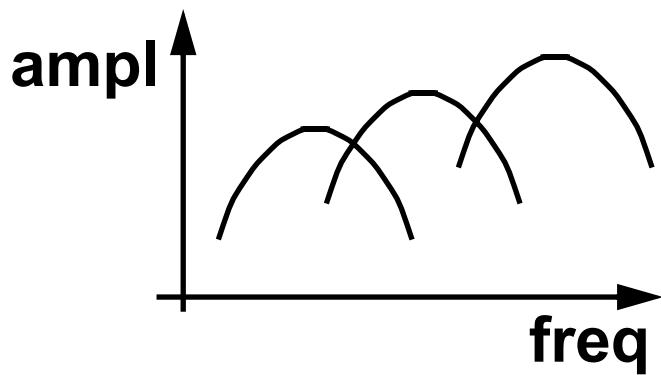
Adjustable Tuning

Adjustable C

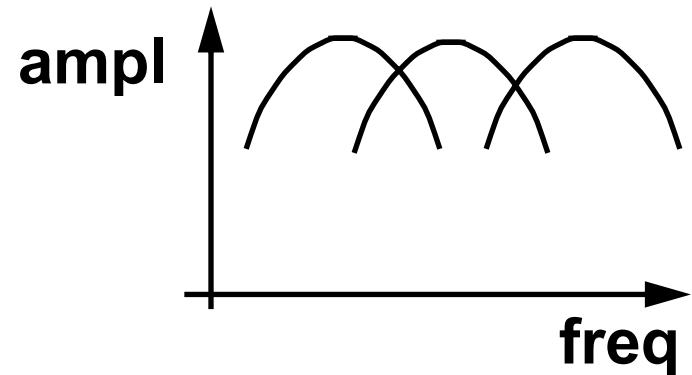
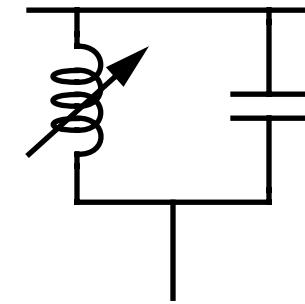


$$R_p = L\omega Q$$

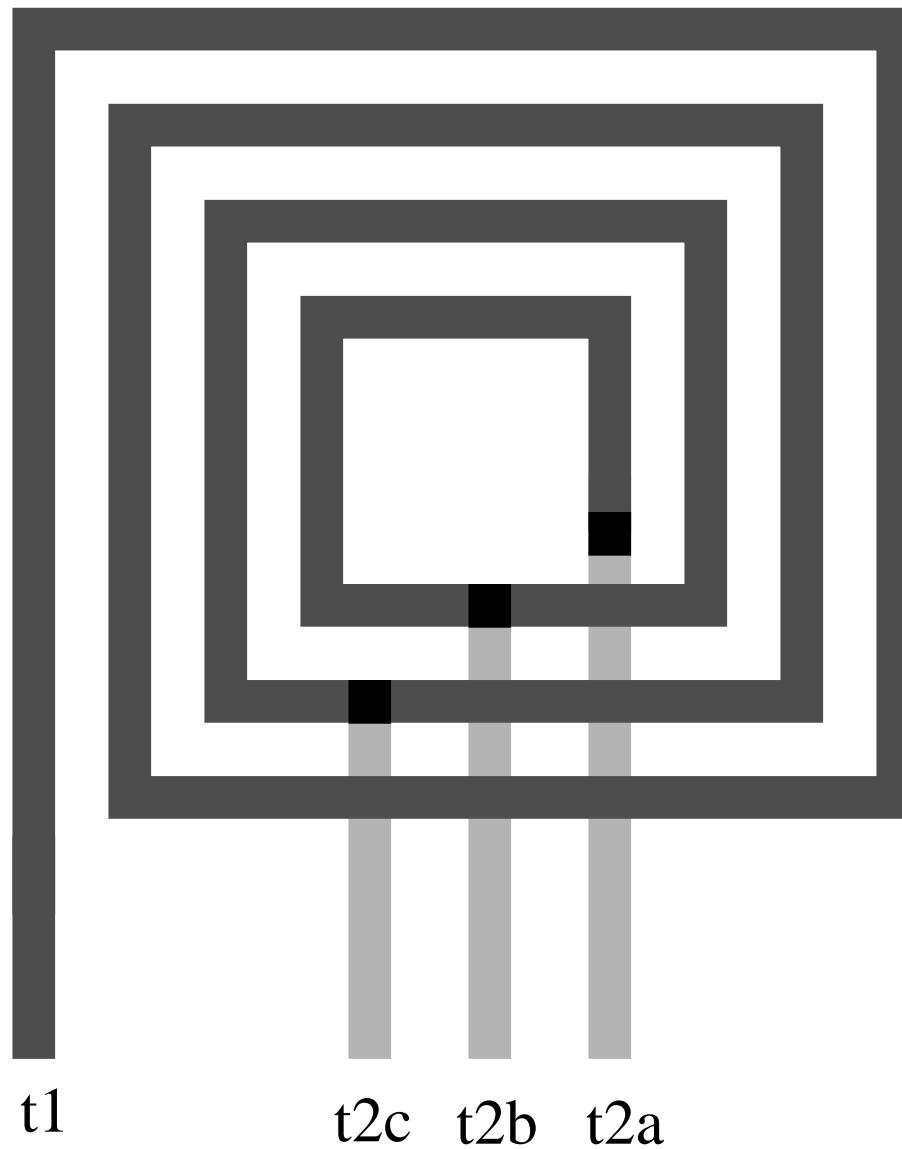
Equivalent parallel resistance



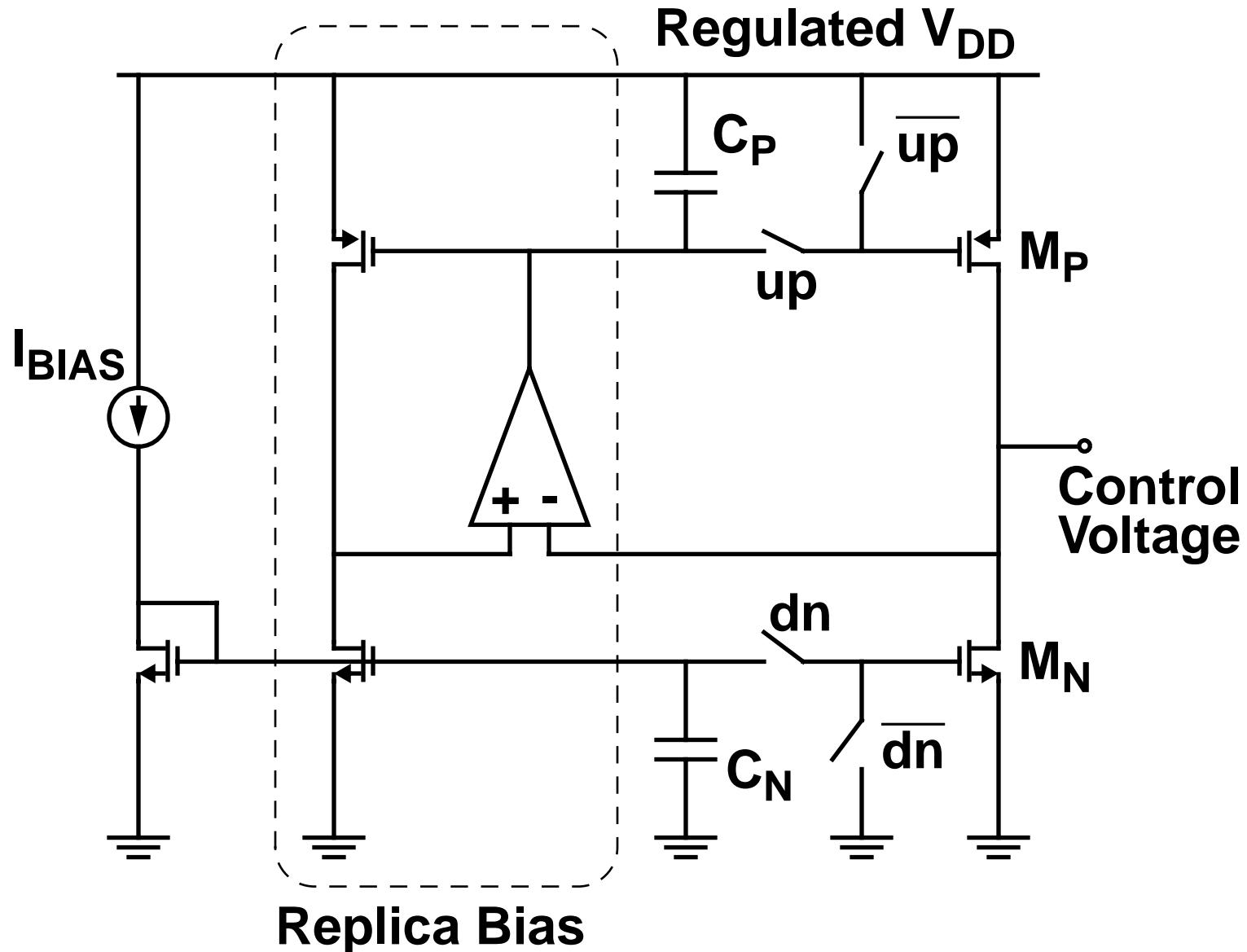
Adjustable L



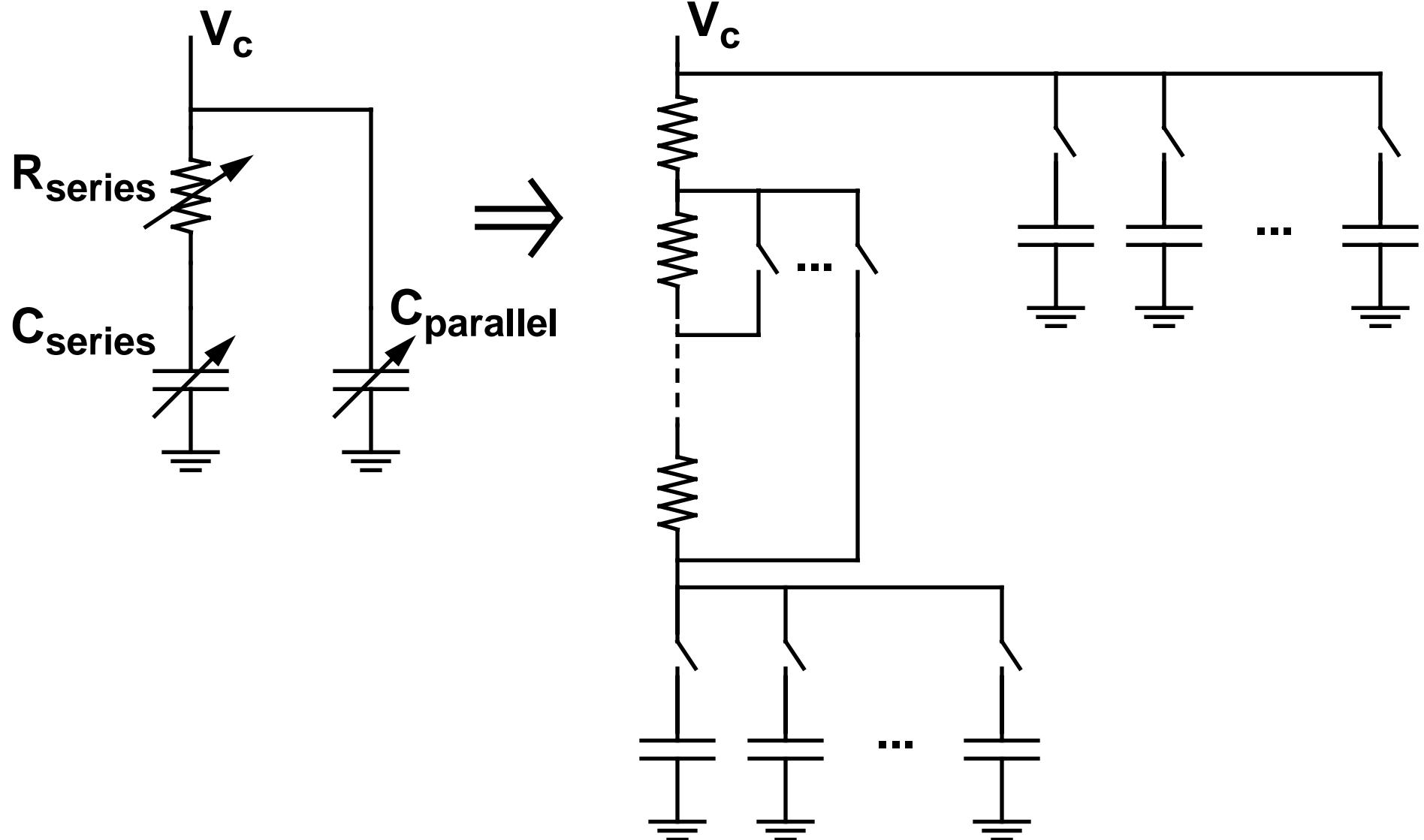
Multi-tap Inductors



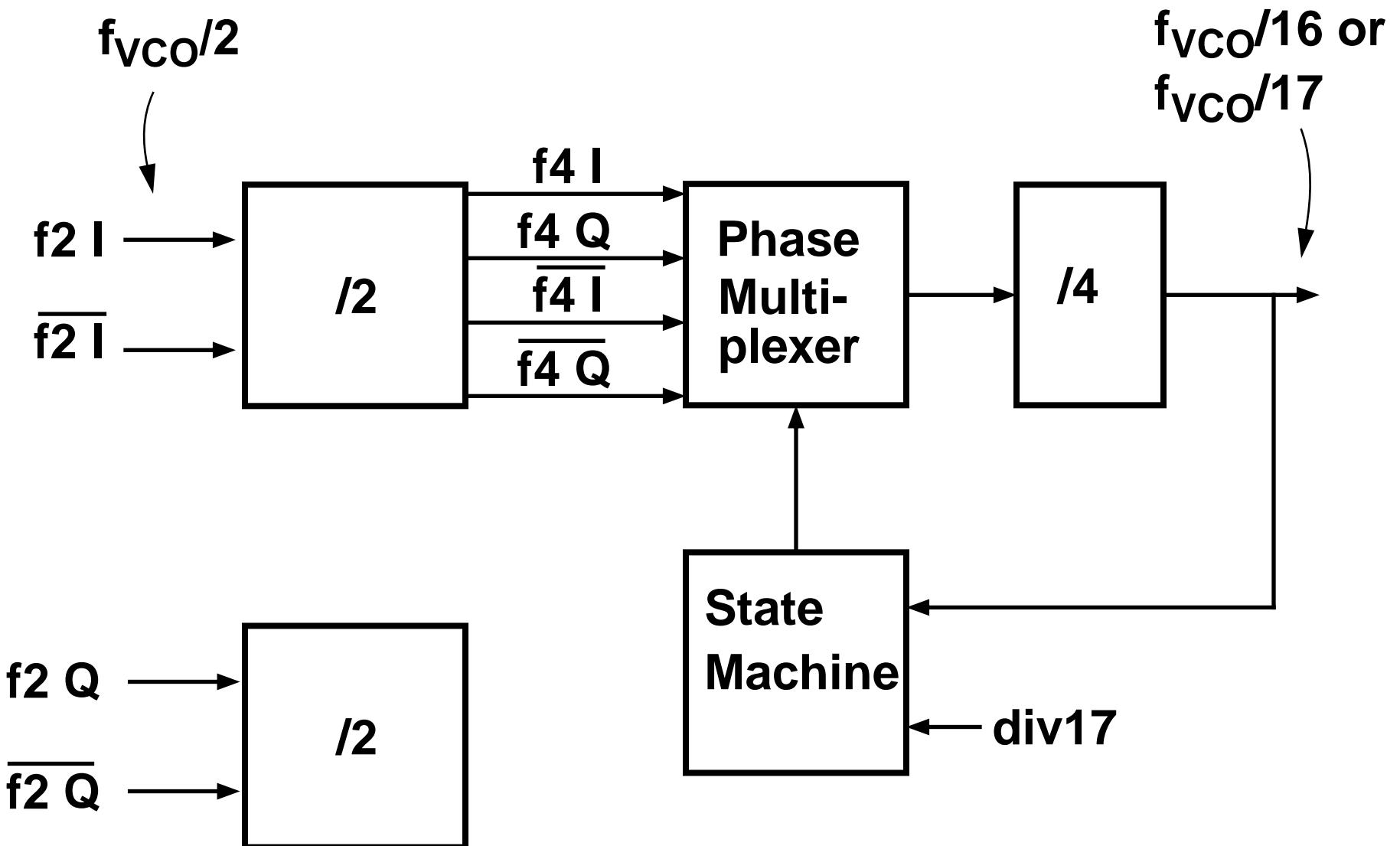
Charge Pump



Programmable Integrated LPF

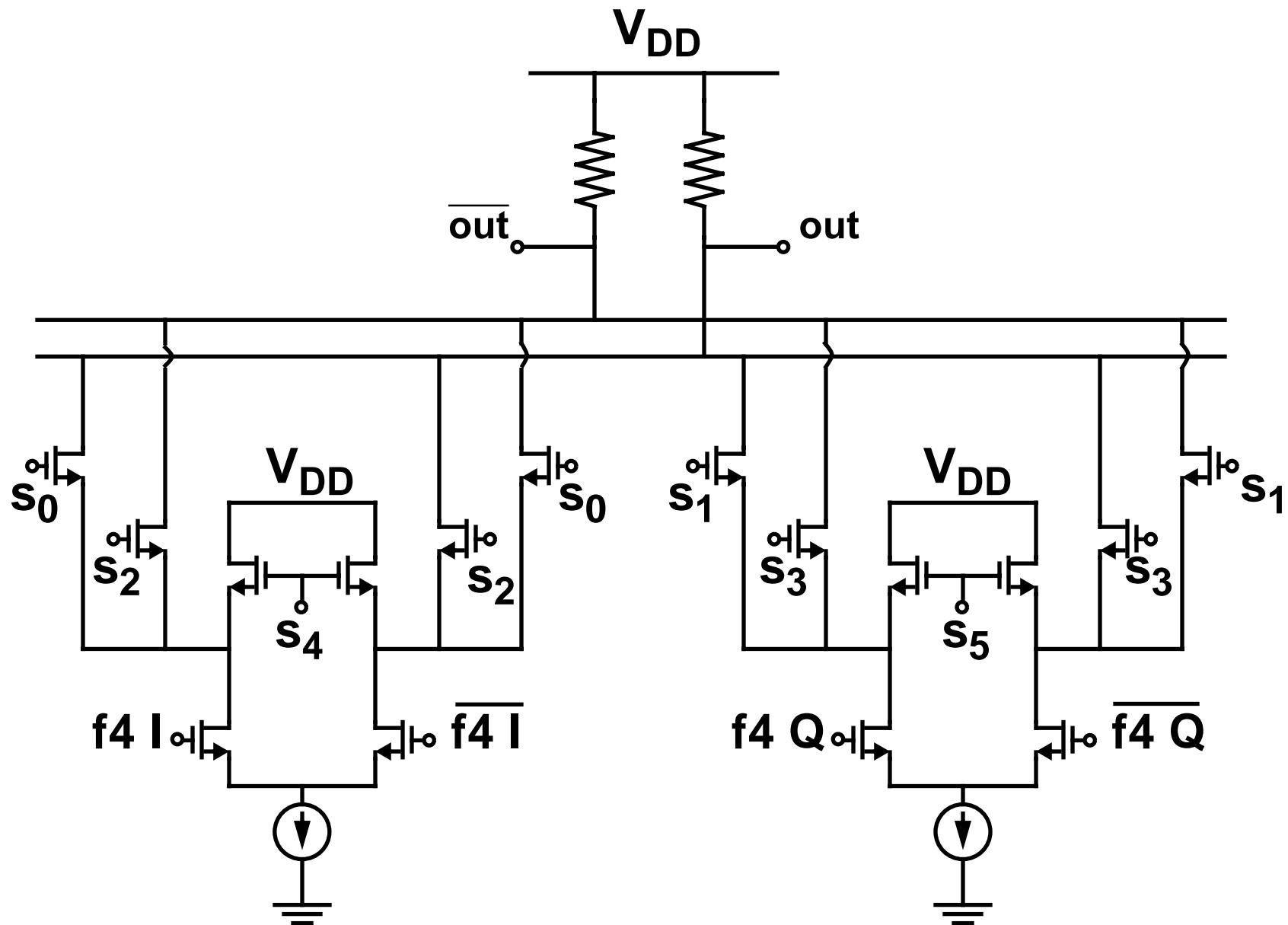


8/8.5 Dual Modulus Divider



J. Craninckx, M. Steyaert “A 1.75-GHz/3-V Dual-Modulus Divide-by-128/129 Prescaler in 0.7- μ m CMOS”, JSSC, July 1996.

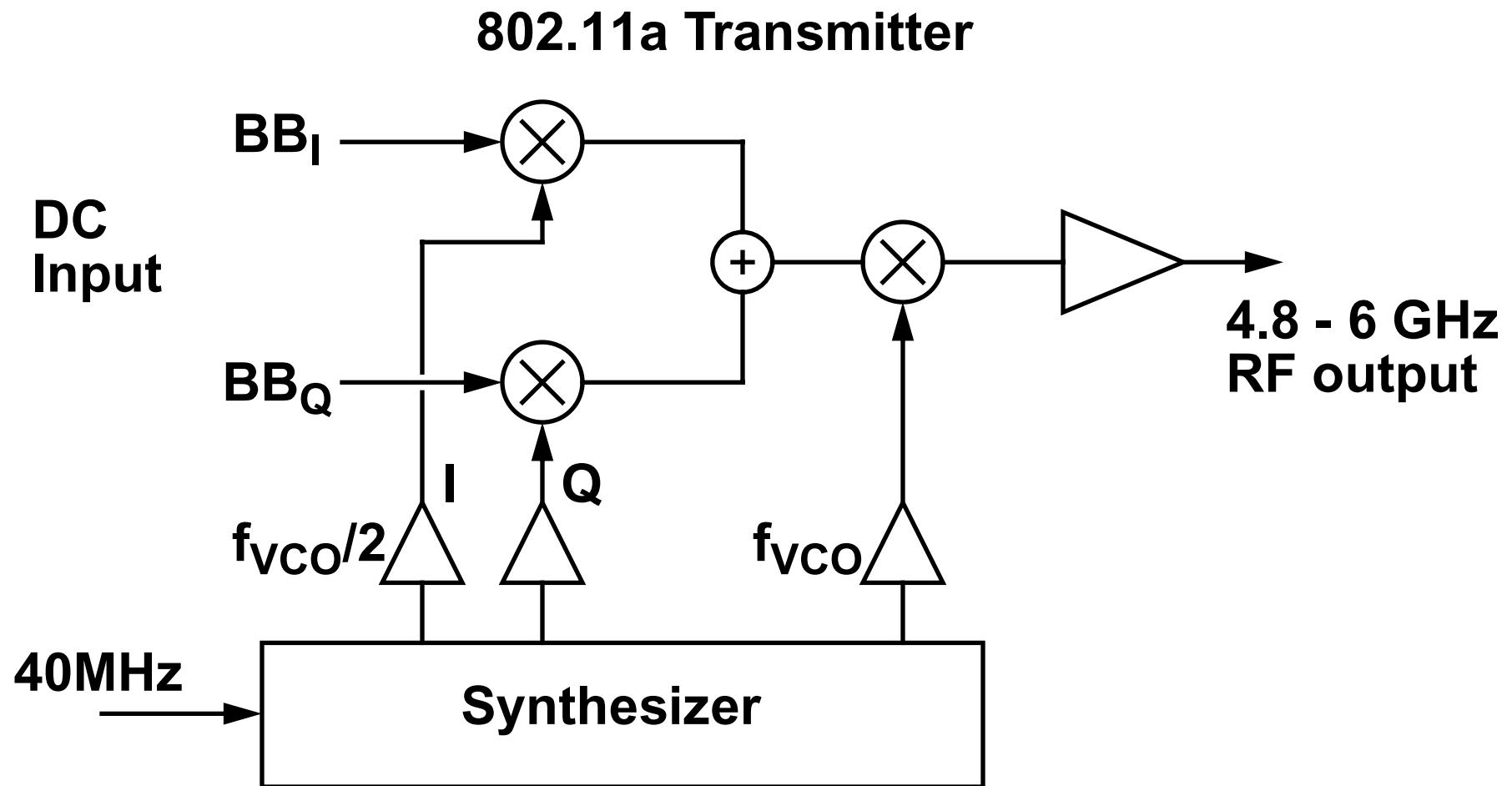
Phase Multiplexer



Control Logic

- Successive approximation search for the 7 bits that control the VCO tuning capacitors
- Coarse digital alignment of the feedback clock with the reference clock
- Optimize for the control voltage value
- Take corrective action when the control voltage drifts out of the acceptable range or when no-lock is detected

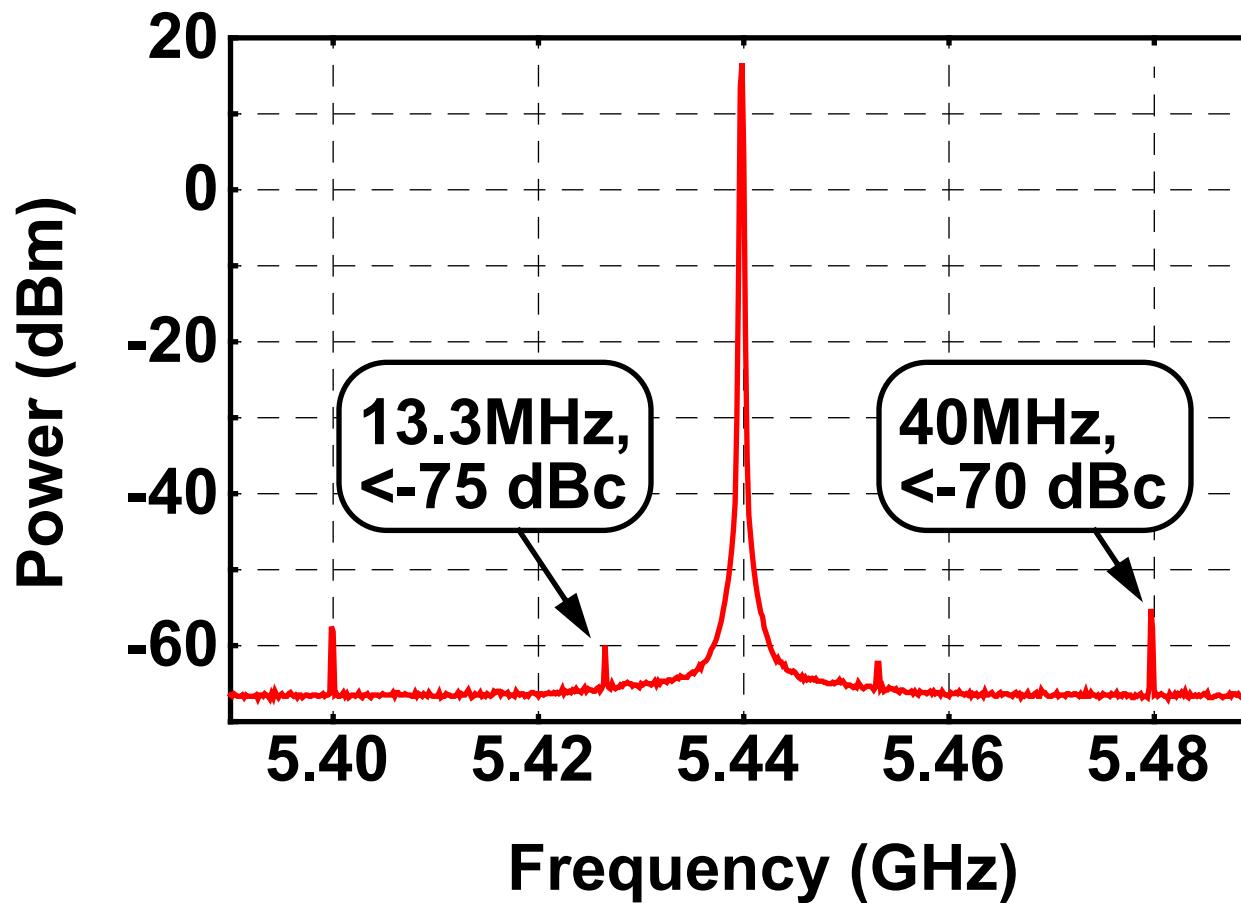
Measurement Setup



- Measured Phase Noise at RF output is ~3.5 dB higher than at the VCO frequency.

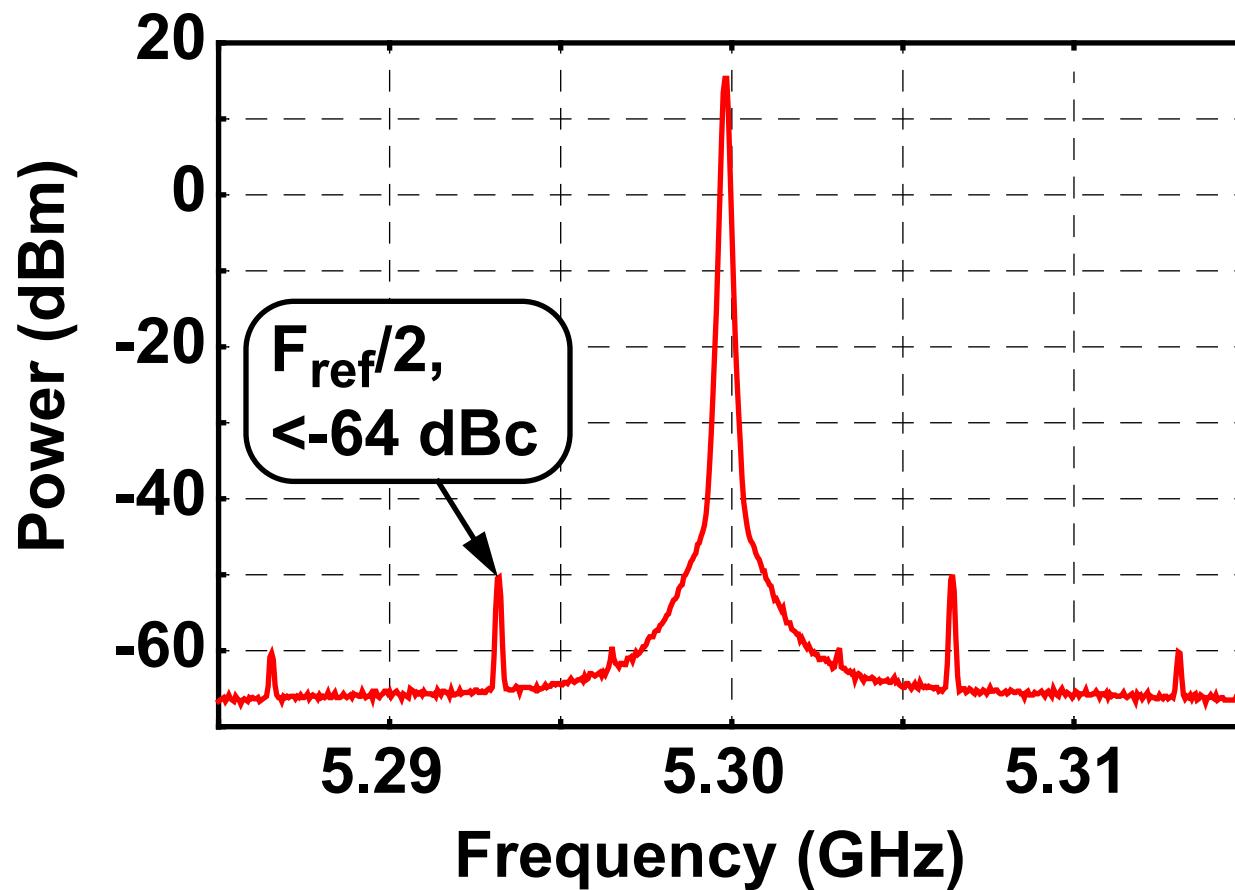
Output Spectrum (1)

$F_o=5.44\text{GHz}$, $F_{\text{ref}}=13.3\text{MHz}$, ($S=0$)



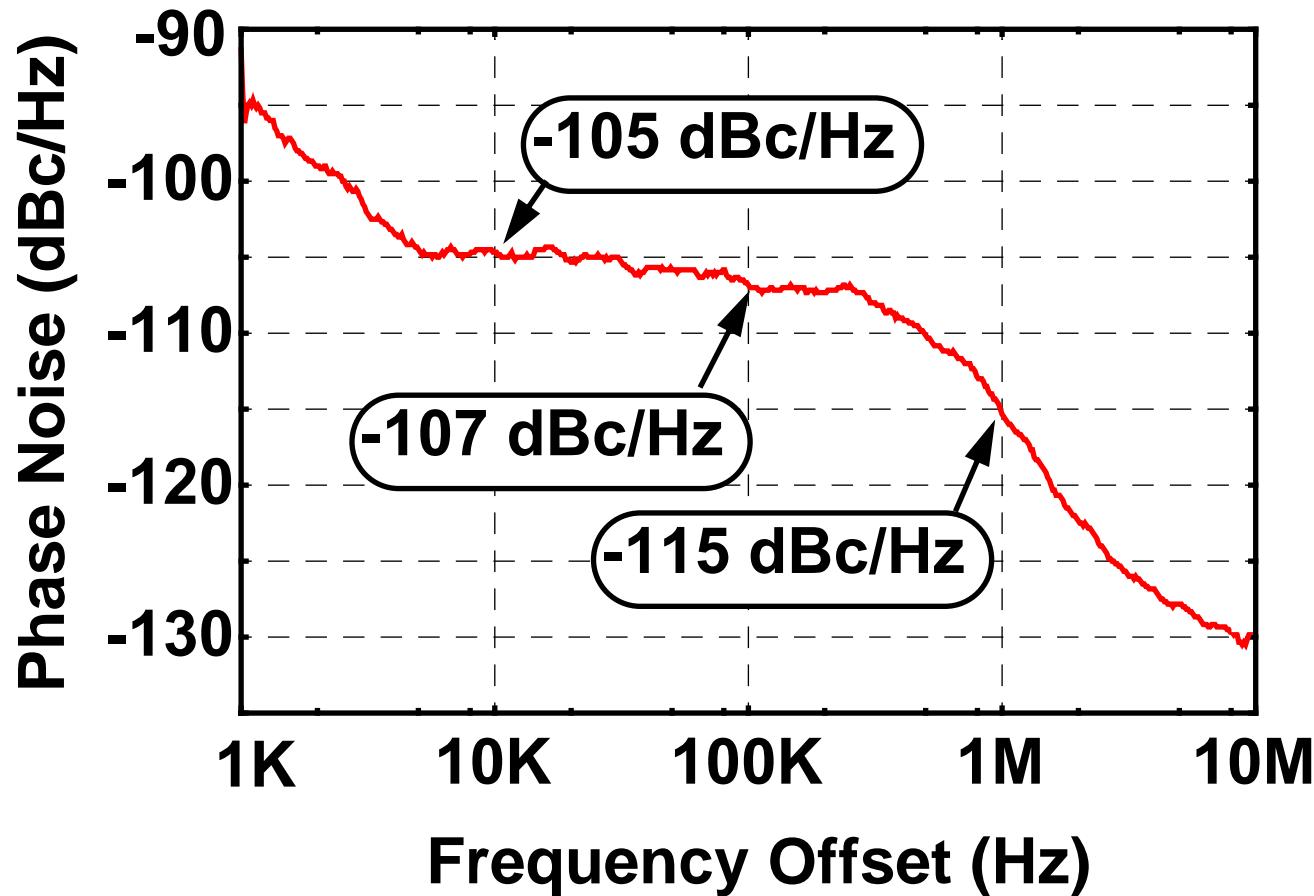
Output Spectrum (2)

$F_o=5.30\text{GHz}$, $F_{\text{ref}}=13.3\text{MHz}$, ($S=9$)

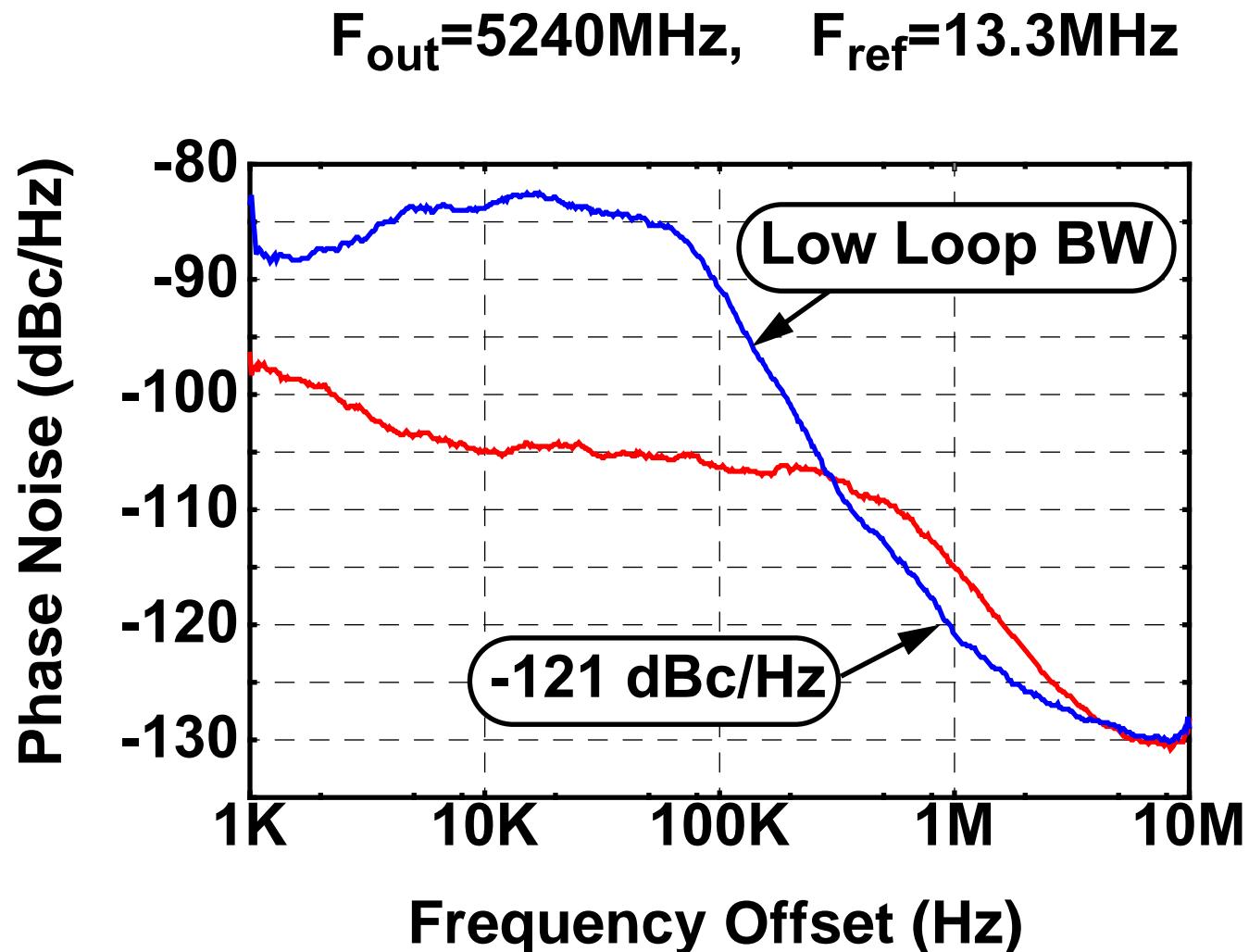


Measured Phase Noise (1)

$F_{\text{out}}=5240\text{MHz}$, $F_{\text{ref}}=13.3\text{MHz}$

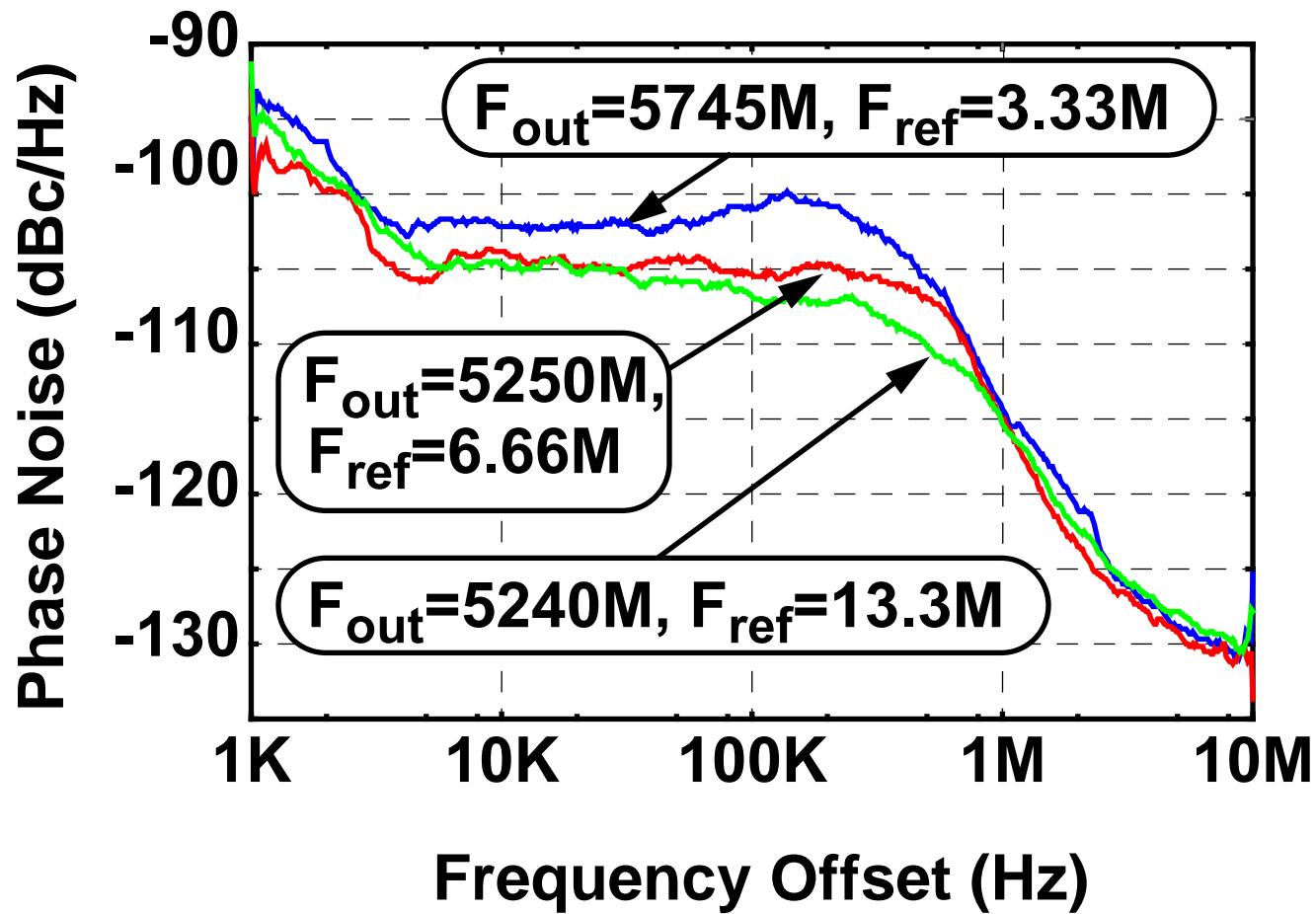


Measured Phase Noise (2)



VCO Phase Noise: -121 dBc/Hz
@ 1MHz offset, 5.24 GHz carrier

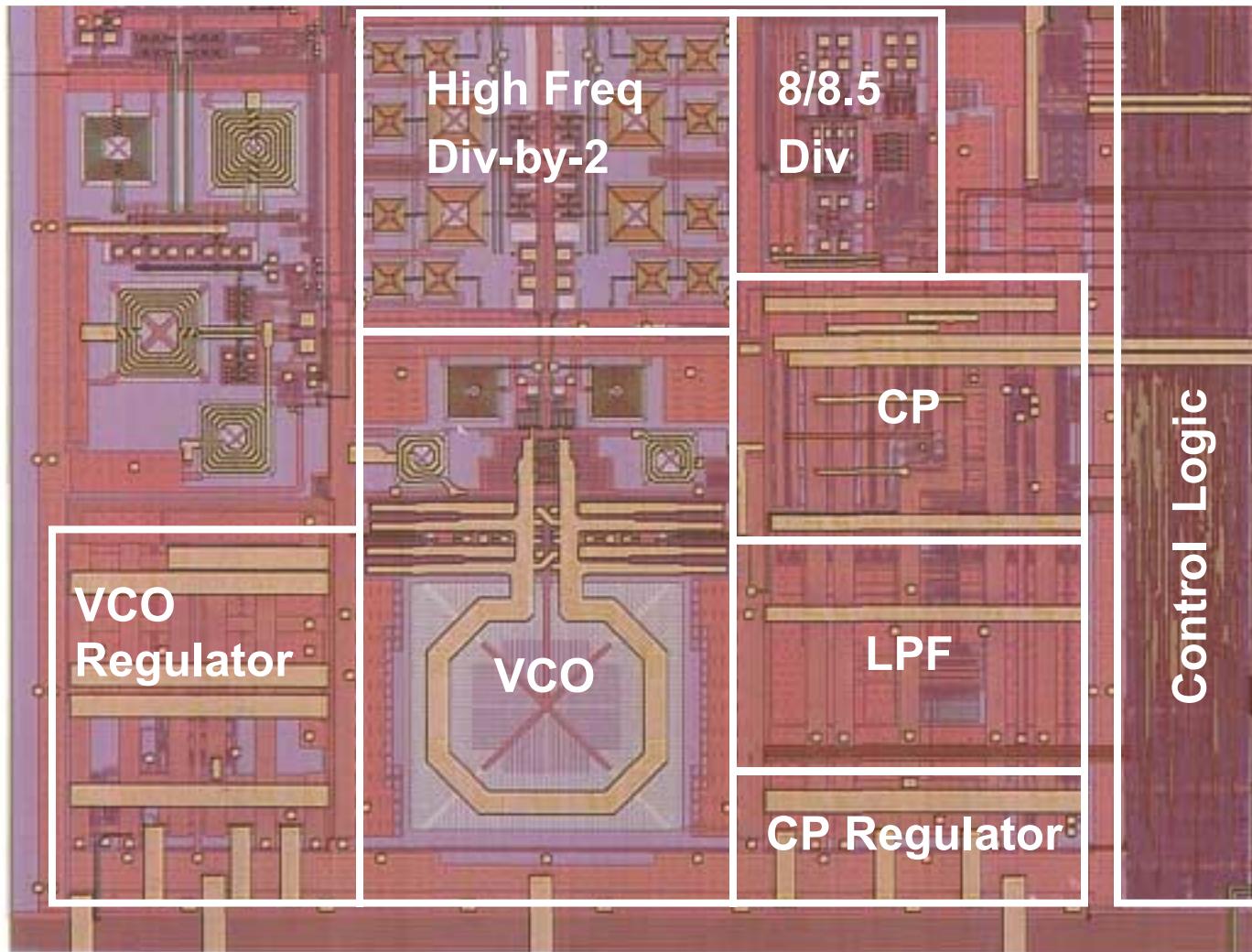
Measured Phase Noise (3)



Performance Summary

Technology	0.25 μ m CMOS, 1P5M, MIM capacitors
Power Dissipation	93 mW
Area	1.7 mm ²
Spot Phase Noise $F_{out} = 5240\text{MHz}$, $F_{ref} = 13.3\text{ MHz}$	-105/-107/-115 dBc/Hz @ 10K/100K/1M
Integrated PN (from 1K to 10M) $F_{out} = 5240\text{MHz}$, $F_{ref} = 13.3\text{ MHz}$ $F_{out} = 5250\text{MHz}$, $F_{ref} = 6.66\text{ MHz}$ $F_{out} = 5745\text{MHz}$, $F_{ref} = 3.33\text{ MHz}$	-45.3 dBc (0.31°) -43.3 dBc (0.40°) -40.9 dBc (0.54°)
Spurs	<-64dBc
Settling Time	<150 μ s

Synthesizer Micrograph



Conclusions

- Fully integrated, wideband, $0.25\mu\text{m}$ CMOS synthesizer
- Excellent phase noise, spur performance and settling time
- Design highlights:
 - On-chip voltage regulation
 - Tuning with switching inductors
 - Low noise VCO
 - Charge pump topology

Acknowledgment

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